

## BAS70-04-05-06 SCHOTTKY DIODE

### FEATURES

Power dissipation

$$P_D: \quad 200 \quad \text{mW} \quad (T_{amb}=25^\circ\text{C})$$

Collector current

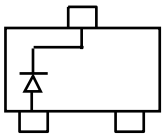
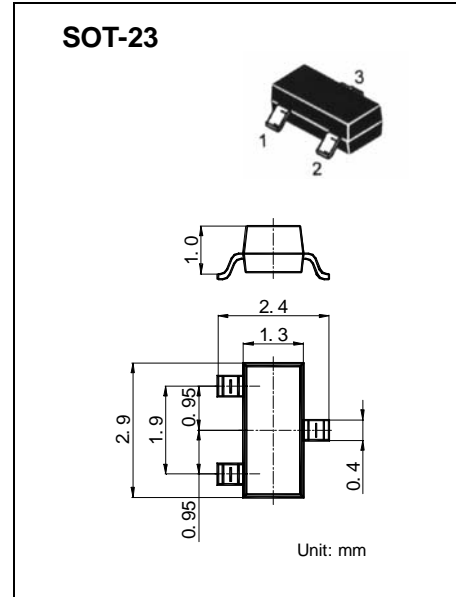
$$I_F: \quad 200 \quad \text{mA}$$

Collector-base voltage

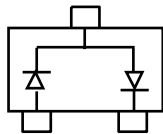
$$V_R: \quad 70 \quad \text{V}$$

Operating and storage junction temperature range

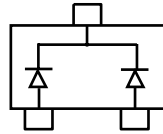
$$T_J, T_{stg}: \quad -55^\circ\text{C} \quad \text{to} \quad +150^\circ\text{C}$$



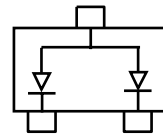
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### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu\text{A}$	70		V
Reverse voltage leakage current	$I_R$	$V_R=50\text{V}$		100	nA
Forward voltage	$V_F$	$I_F=1\text{mA}$ $I_F=15\text{mA}$		410 1000	mV
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		2	pF
Reveres recovery time	$t_{rr}$	$I_F=10\text{mA}$ through $I_R=10\text{mA}$ to $I_R=1\text{mA}$		5	nS